

ABSTRACT OF THE DISCLOSURE

A method of measuring a concentration of dopants of an objective thin film includes measuring a concentration of dopants of a first wafer, forming the objective thin film on the first wafer to form a second wafer, measuring a concentration of dopants of the second wafer, and obtaining the concentration of dopants of the objective thin film by subtracting the concentration of dopants of the first wafer from the concentration of dopants of the second wafer. Therefore, the concentration of dopants of the objective thin film may be measured without the use of a criterion wafer, thereby reducing measuring time. Also, the concentration of dopants of the objective thin film may be easily controlled, and therefore promptly corrected if necessary.